/ Descriptions

WR0<50P ṂṂÞ QSQ ÆṀч s ‖ ㄱ Silicon NPN transistor in a TO-92LM Plastic Package.

/ Features

F0E ڑ ↄ я ᙏ ı ļ ' ᙏ

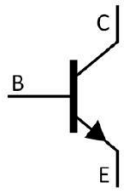
High Collector-Base Voltage, high Current Gain Bandwidth Product.

/ Applications

ᵮ ᙏ я ı ' ѽ ᶻ

High voltage power amplifier.

/ Equivalent Circuit



/ Pinning



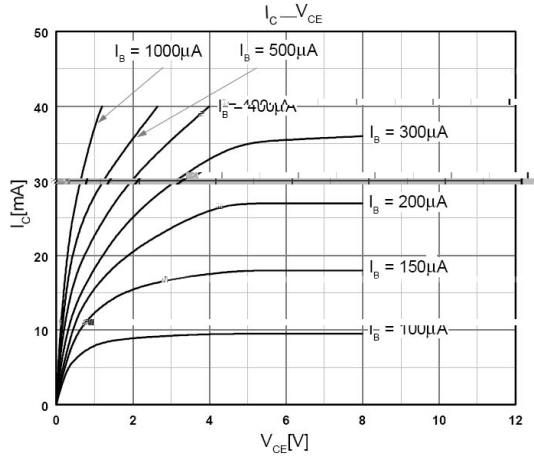
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

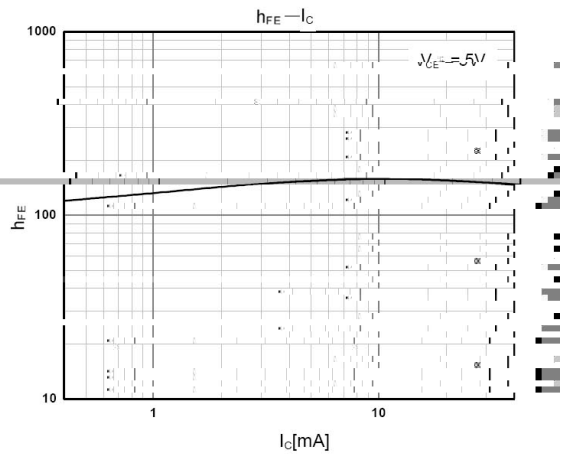
/ h_{FE} Classifications & Marking

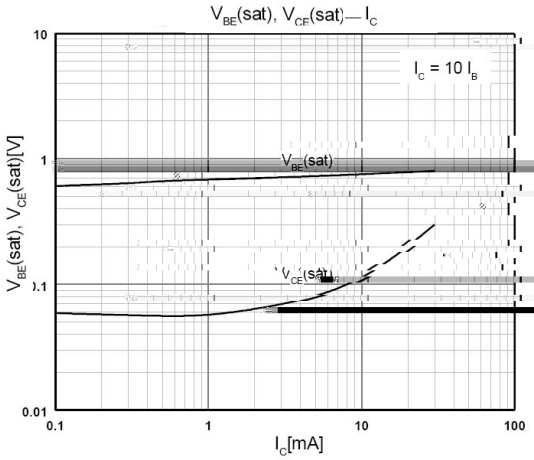
h_{FE} Classifications Symbol	R	O	Y
h_{FE} Range	40 80	70 140	120 240

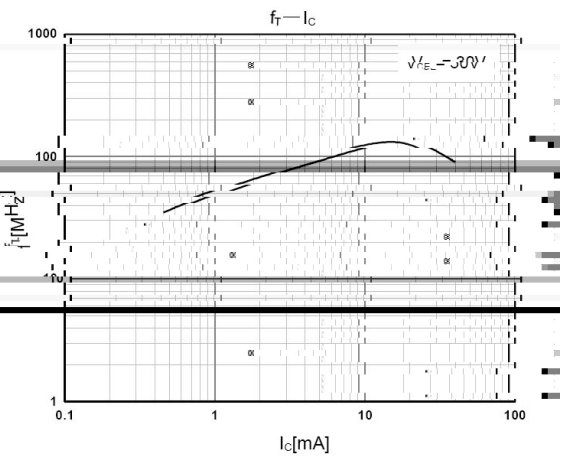
v ‴Ω Parameter	ϒ N Symbol	‴Ω Ö Rating	D Ђ Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	150	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	50	mA
i Collector Power Dissipation o t c e P_C l	l 800 o C	mW E C	

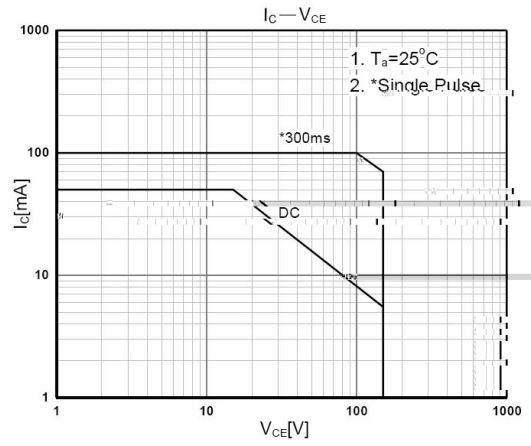
/ Electrical Characteristic Curve

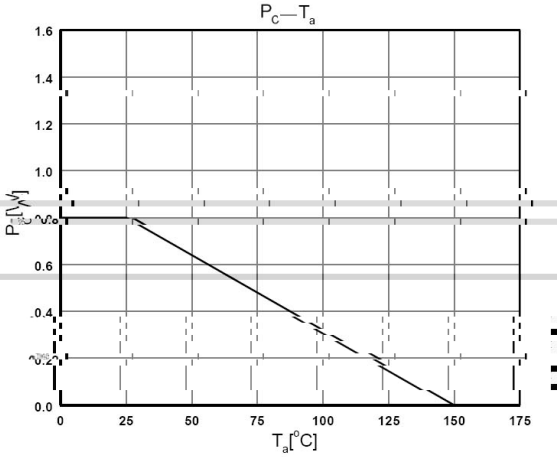






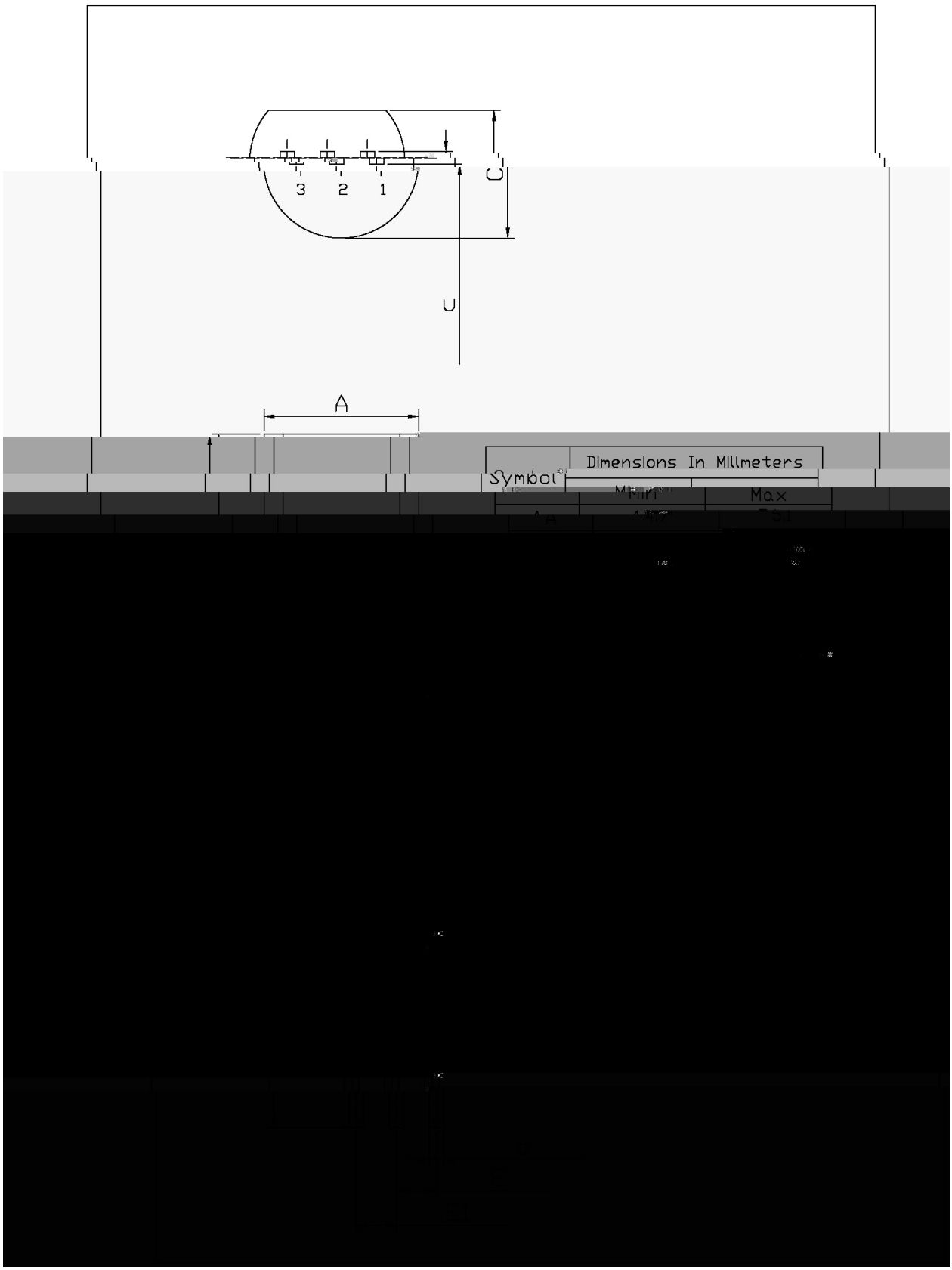






/ Package Dimensions

TO-92LM Unit: mm



( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ɬ ı `H ڑ `Y ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ ｲ ˛ ɔ ๛ ỷ ㎞ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

¨Ω ţ ｲ Ł / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

ﾊ Ⅴ ｲ Ł / AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 大箱

/ Notices